MOSFETs Silicon N-channel MOS (U-MOSⅧ-H)

TPH4R10ANL

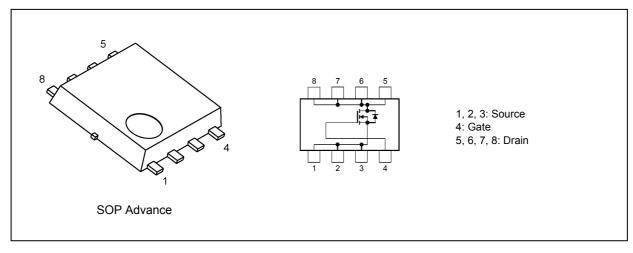
1. Applications

- High-Efficiency DC-DC Converters
- Switching Voltage Regulators
- Motor Drivers

2. Features

- (1) High-speed switching
- (2) Small gate charge : $Q_{SW} = 21 \text{ nC}$ (typ.)
- (3) Small output charge : $Q_{oss} = 74 \text{ nC}$ (typ.)
- (4) Low drain-source on-resistance : $R_{DS(ON)}$ =3.3 mO (typ.)(V_{GS} = 10 V)
- (5) Low leakage current : I_{DSS} = 10 μA (max)(V_{DS} = 100 V)
- (6) Enhancement mode : V_{th} = 1.5 to 2.5 V (V_{DS} = 10 V, I_D = 1.0 mA)

3. Packaging and Internal Circuit



4. Absolute Maximum Ratings (Note) (T_a = 25 °C unless otherwise specified)

Characterist	Symbol	Rating	Unit		
Drain-source voltage			V _{DSS}	100	V
Gate-source voltage			V _{GSS}	±20	
Drain current (DC)	(T _c = 25 °C)	(Note 1)	Ι _D	70	A
Drain current (DC)	(Silicon limit)	(Note 1), (Note 2)	Ι _D	92	
Drain current (pulsed)	(t = 100 µs)	(Note 1)	I _{DP}	490	
Power dissipation	(T _c = 25 °C)		PD	67	W
Power dissipation		(Note 3)	PD	2.5	
Power dissipation		(Note 4)	PD	0.8	
Single-pulse avalanche energy		(Note 5)	E _{AS}	118	mJ
Single-pulse avalanche current		(Note 5)	I _{AS}	70	A
Channel temperature			T _{ch}	150	°C
Storage temperature			T _{stg}	-55 to 150	

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

5. Thermal Characteristics

Characteristics	Symbol	Max	Unit		
Channel-to-case thermal resistance	(T _c = 25 °C)		R _{th(ch-c)}	1.86	°C/W
Channel-to-ambient thermal resistance	(T _a = 25 °C)	(Note 3)	R _{th(ch-a)}	50	
Channel-to-ambient thermal resistance	(T _a = 25 °C)	(Note 4)	R _{th(ch-a)}	156	

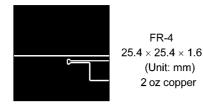
Note 1: Ensure that the channel temperature does not exceed 150 °C.

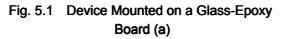
Note 2: Limited by silicon chip capability.

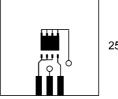
Note 3: Device mounted on a glass-epoxy board (a), Figure 5.1

Note 4: Device mounted on a glass-epoxy board (b), Figure 5.2

Note 5: V_DD = 60 V, T_ch = 25 °C (initial), L = 26 $\mu H, \, I_{AS}$ = 70 A







FR-4 25.4 × 25.4 × 1.6 (Unit: mm) 2 oz copper

Fig. 5.2 Device Mounted on a Glass-Epoxy Board (b)

Note: This transistor is sensitive to electrostatic discharge and should be handled with care.

6. Electrical Characteristics

6.1. Static Characteristics (Ta = 25 °C unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Gate leakage current	I _{GSS}	V_{GS} = ±20 V, V_{DS} = 0 V		—	±0.1	μA
Drain cut-off current	I _{DSS}	V _{DS} = 100 V, V _{GS} = 0 V		_	10	
Drain-source breakdown voltage	V _{(BR)DSS}	I _D = 10 mA, V _{GS} = 0 V	100	_	—	V
Drain-source breakdown voltage (Note 6)	V _{(BR)DSX}	I _D = 10 mA, V _{GS} = -20 V	65	_	_	
Gate threshold voltage	V _{th}	V _{DS} = 10 V, I _D = 1.0 mA	1.5	_	2.5	
Drain-source on-resistance	R _{DS(ON)}	V _{GS} = 4.5 V, I _D = 20 A		4.1	6.6	mΩ
		V _{GS} = 10 V, I _D = 35 A		3.3	4.1	

Note 6: If a reverse bias is applied between gate and source, this device enters V_{(BR)DSX} mode. Note that the drainsource breakdown voltage is lowered in this mode.

6.2. Dynamic Characteristics ($T_a = 25$ °C unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Input capacitance	C _{iss}	V _{DS} = 50 V, V _{GS} = 0 V,	_	4850	6300	pF
Reverse transfer capacitance	C _{rss}	f = 1 MHz	_	29	59	
Output capacitance	C _{oss}		_	640	—	
Gate resistance	r _g		_	2.1	3.2	Ω
Switching time (rise time)	t _r	See Figure 6.2.1	_	8.0	—	ns
Switching time (turn-on time)	t _{on}		_	20	—	
Switching time (fall time)	t _f]		15	_	
Switching time (turn-off time)	t _{off}		_	71	_	

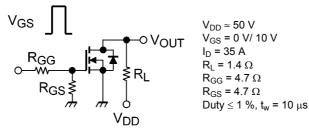


Fig. 6.2.1 Switching Time Test Circuit

6.3. Gate Charge Characteristics ($T_a = 25$ °C unless otherwise specified)

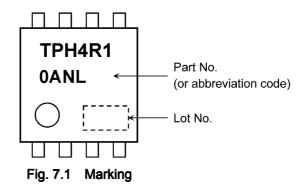
Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Total gate charge (gate-source plus gate-drain)	Qg	$V_{DD} \approx 50 \text{ V}, \text{ V}_{GS} = 10 \text{ V},$ $I_D = 35 \text{ A}$	_	75	_	nC
		$V_{DD} \approx 50 \text{ V}, \text{ V}_{GS} = 4.5 \text{ V},$ I_D = 35 A	_	37	_	
Gate-source charge 1	Q _{gs1}	$V_{DD} \approx 50 \text{ V}, V_{GS} = 10 \text{ V},$ $I_D = 35 \text{ A}$	_	19	—	
Gate-drain charge	Q _{gd}		_	12	_	
Gate switch charge	Q _{SW}		_	21	_	
Output charge	Q _{oss}	V _{DS} = 50 V, V _{GS} = 0 V, f = 1 MHz		74		

6.4. Source-Drain Characteristics ($T_a = 25$ °C unless otherwise specified)

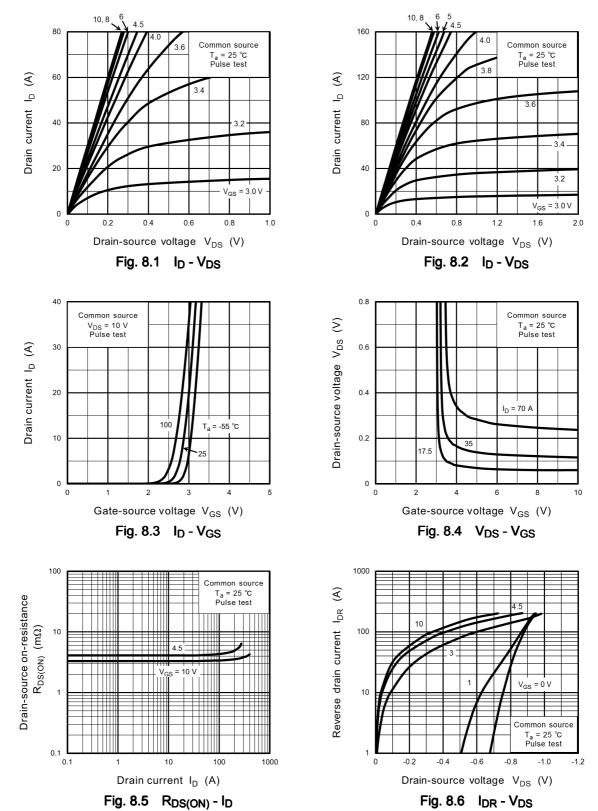
Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Reverse drain current (pulsed) (Note	') I _{DRP}	(t = 100 µs)	_	—	490	A
Diode forward voltage	V _{DSF}	I _{DR} = 70 A, V _{GS} = 0 V	_	_	-1.2	V
Reverse recovery time	t _{rr}	I _{DR} = 17.5 A, V _{GS} = 0 V,	_	52	_	ns
Reverse recovery charge	Q _{rr}	-dI _{DR} /dt = 100 A/μs		78	_	nC

Note 7: Ensure that the channel temperature does not exceed 150 °C.

7. Marking



8. Characteristics Curves (Note)



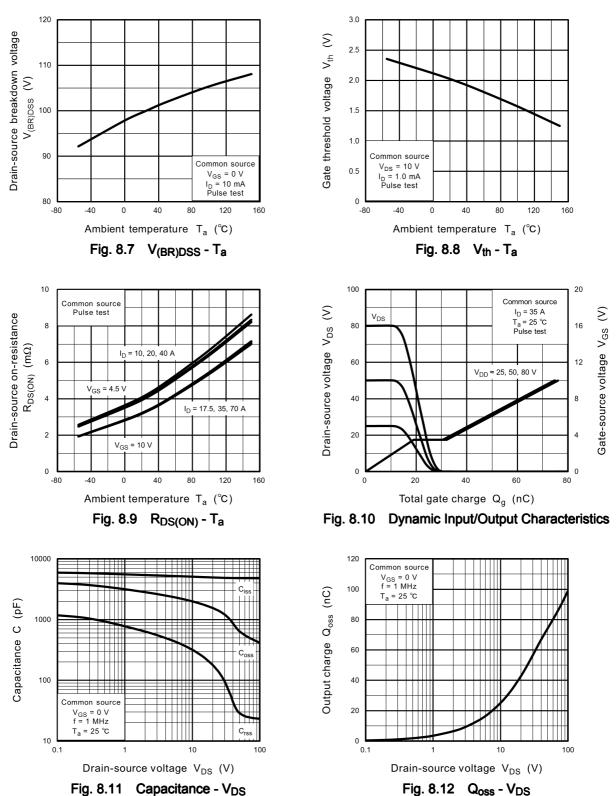
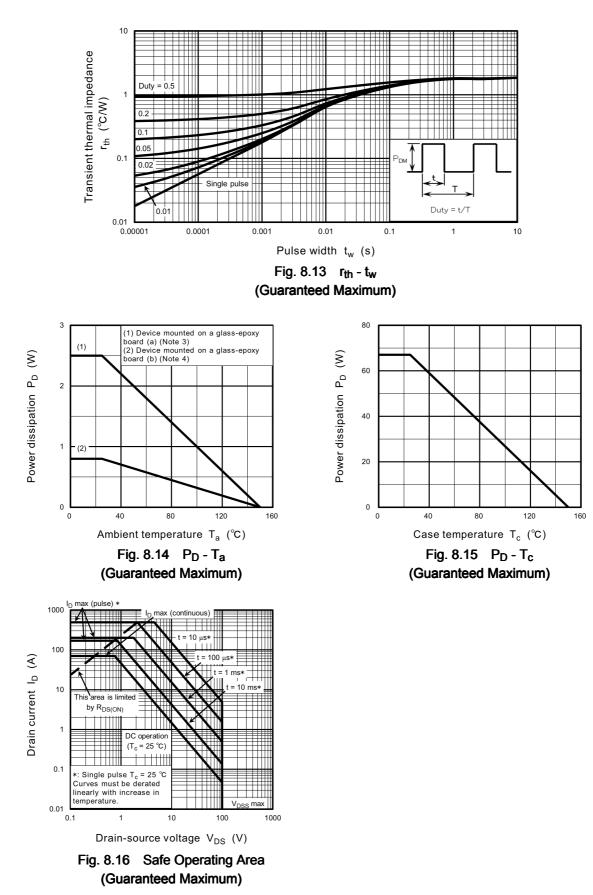


Fig. 8.11 Capacitance - VDS

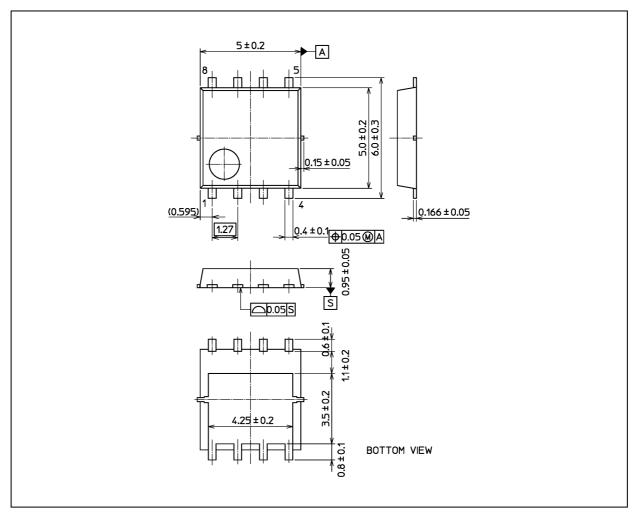


Note: The above characteristics curves are presented for reference only and not guaranteed by production test, unless otherwise noted.

TPH4R10ANL

Package Dimensions

Unit: mm



Weight: 0.087 g (typ.)

TOSHIBA: 2-5Q1S

Nickname: SOP Advance

Package Name(s)

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